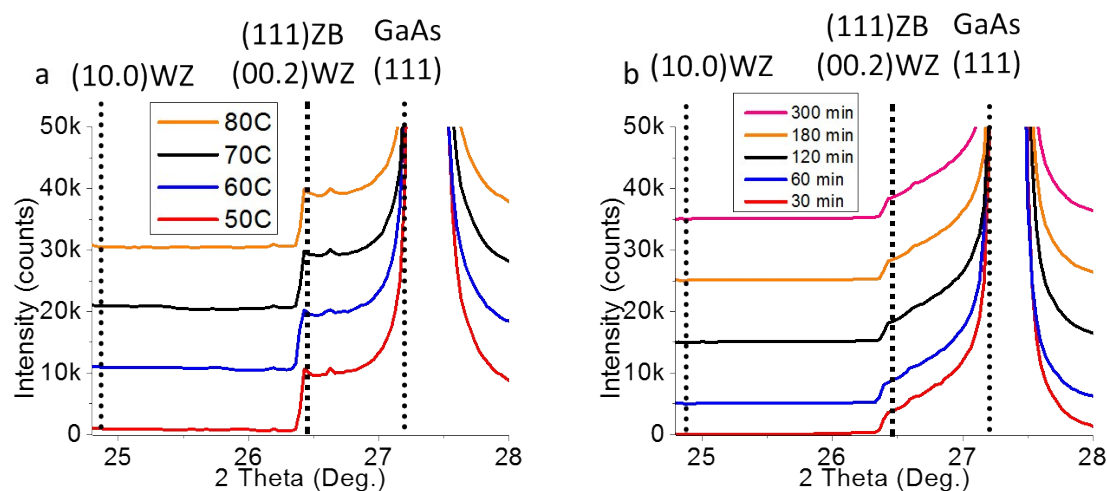


## Electronic Supplementary information

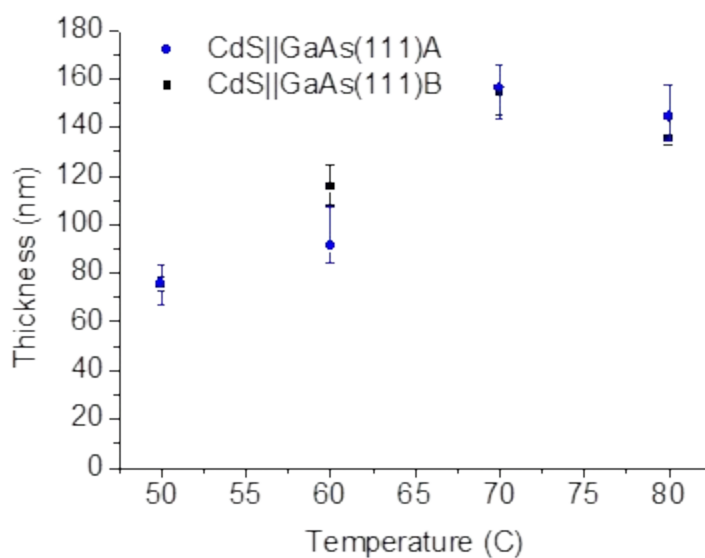
### Chemical Epitaxy of CdS on GaAs

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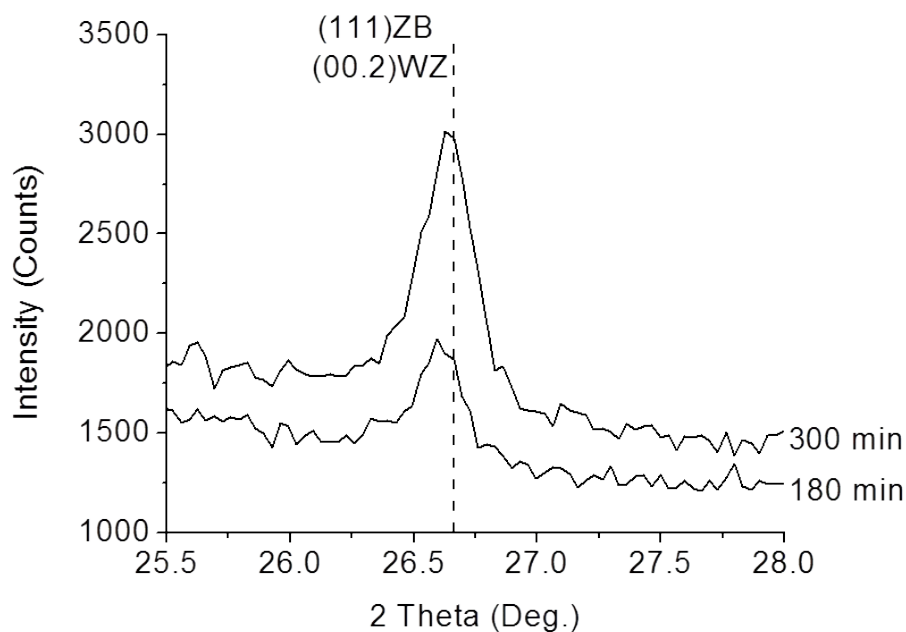
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**Fig. S1** XRD pattern of CdS deposited on GaAs(111)A using 7.5 mM CdSO<sub>4</sub>. (a) Effect of temperature for 2 hr of deposition. (b) Effect of deposition duration at a temperature of 60°C.



**Fig. S2** Film thickness measurements extracted from cross-section HR-SEM from CdS deposited on GaAs(111)A (blue) and GaAs(111)B (black) using 7.5 mM CdSO<sub>4</sub> for a duration of 2 hr.



**Fig. S3** XRD pattern of CdS deposited on glass substrates using 5 mM CdSO<sub>4</sub>, deposition temperature of 60°C, and deposition duration of 180 and 300 min.